

# IRG4BC20FDPbF

INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST  
SOFT RECOVERY DIODE

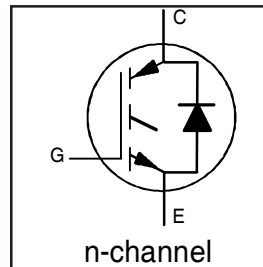
Fast CoPack IGBT

## Features

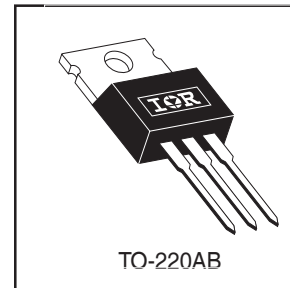
- Fast: optimized for medium operating frequencies ( 1-5 kHz in hard switching, >20 kHz in resonant mode).
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220AB package
- Lead-Free

## Benefits

- Generation -4 IGBTs offer highest efficiencies available
- IGBTs optimized for specific application conditions
- HEXFRED diodes optimized for performance with IGBTs. Minimized recovery characteristics require less/no snubbing
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBTs



|                                   |
|-----------------------------------|
| $V_{CES} = 600V$                  |
| $V_{CE(on)} \text{ typ.} = 1.66V$ |
| @ $V_{GE} = 15V, I_C = 9.0A$      |



## Absolute Maximum Ratings

|                           | Parameter                          | Max.                              | Units      |
|---------------------------|------------------------------------|-----------------------------------|------------|
| $V_{CES}$                 | Collector-to-Emitter Voltage       | 600                               | V          |
| $I_C @ T_C = 25^\circ C$  | Continuous Collector Current       | 16                                | A          |
| $I_C @ T_C = 100^\circ C$ | Continuous Collector Current       | 9.0                               |            |
| $I_{CM}$                  | Pulsed Collector Current ①         | 64                                |            |
| $I_{LM}$                  | Clamped Inductive Load Current ②   | 64                                |            |
| $I_F @ T_C = 100^\circ C$ | Diode Continuous Forward Current   | 7.0                               |            |
| $I_{FM}$                  | Diode Maximum Forward Current      | 32                                |            |
| $V_{GE}$                  | Gate-to-Emitter Voltage            | $\pm 20$                          | V          |
| $P_D @ T_C = 25^\circ C$  | Maximum Power Dissipation          | 60                                | W          |
| $P_D @ T_C = 100^\circ C$ | Maximum Power Dissipation          | 24                                |            |
| $T_J$                     | Operating Junction and             | -55 to +150                       | $^\circ C$ |
| $T_{STG}$                 | Storage Temperature Range          |                                   |            |
|                           | Soldering Temperature, for 10 sec. | 300 (0.063 in. (1.6mm) from case) |            |
|                           | Mounting Torque, 6-32 or M3 Screw. | 10 lbf•in (1.1 N•m)               |            |

## Thermal Resistance

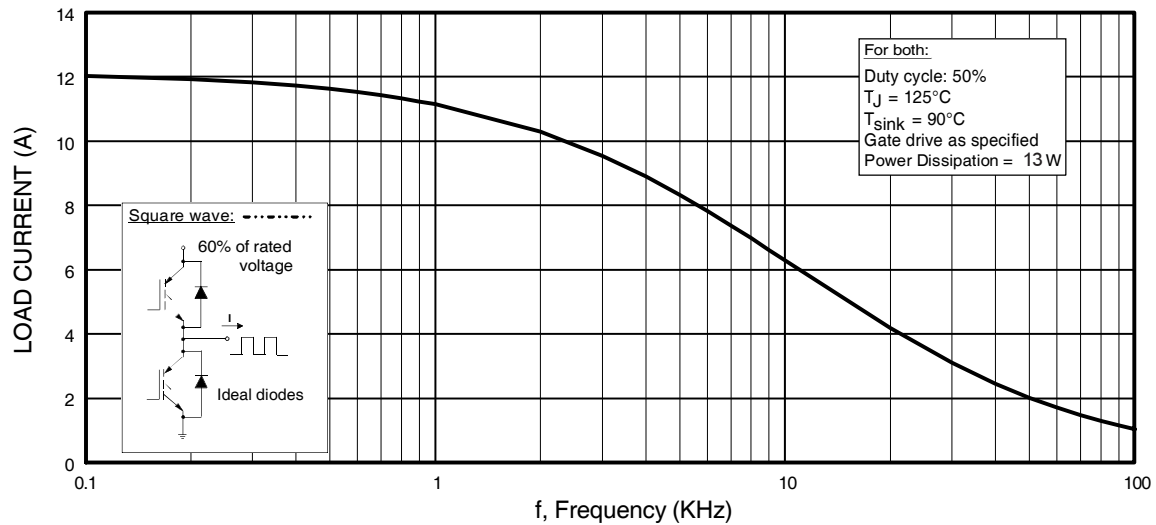
|                 | Parameter                                 | Min. | Typ.     | Max. | Units        |
|-----------------|-------------------------------------------|------|----------|------|--------------|
| $R_{\theta JC}$ | Junction-to-Case - IGBT                   | —    | —        | 2.1  | $^\circ C/W$ |
| $R_{\theta JC}$ | Junction-to-Case - Diode                  | —    | —        | 3.5  |              |
| $R_{\theta CS}$ | Case-to-Sink, flat, greased surface       | —    | 0.50     | —    |              |
| $R_{\theta JA}$ | Junction-to-Ambient, typical socket mount | —    | —        | 80   |              |
| $Wt$            | Weight                                    | —    | 2 (0.07) | —    | g (oz)       |

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

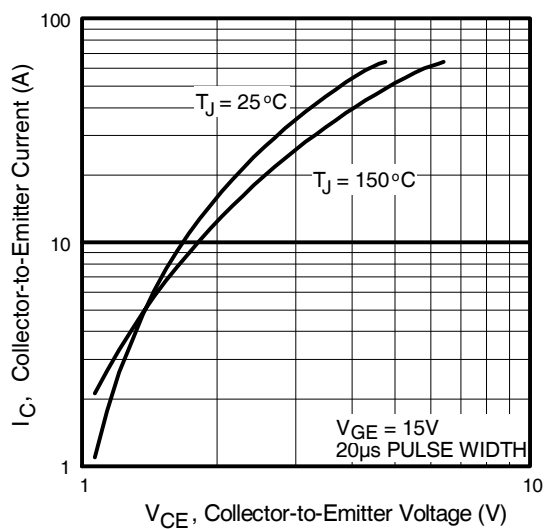
|                                 | Parameter                                           | Min. | Typ. | Max.      | Units                | Conditions                                            |
|---------------------------------|-----------------------------------------------------|------|------|-----------|----------------------|-------------------------------------------------------|
| $V_{(BR)CES}$                   | Collector-to-Emitter Breakdown Voltage <sup>③</sup> | 600  | —    | —         | V                    | $V_{GE} = 0V, I_C = 250\mu A$                         |
| $\Delta V_{(BR)CES}/\Delta T_J$ | Temperature Coeff. of Breakdown Voltage             | —    | 0.72 | —         | V/ $^\circ\text{C}$  | $V_{GE} = 0V, I_C = 1.0mA$                            |
| $V_{CE(on)}$                    | Collector-to-Emitter Saturation Voltage             | —    | 1.66 | 2.0       | V                    | $I_C = 9.0A$ $V_{GE} = 15V$                           |
|                                 |                                                     | —    | 2.06 | —         |                      | $I_C = 16A$ See Fig. 2, 5                             |
|                                 |                                                     | —    | 1.76 | —         |                      | $I_C = 9.0A, T_J = 150^\circ\text{C}$                 |
| $V_{GE(th)}$                    | Gate Threshold Voltage                              | 3.0  | —    | 6.0       |                      | $V_{CE} = V_{GE}, I_C = 250\mu A$                     |
| $\Delta V_{GE(th)}/\Delta T_J$  | Temperature Coeff. of Threshold Voltage             | —    | -11  | —         | mV/ $^\circ\text{C}$ | $V_{CE} = V_{GE}, I_C = 250\mu A$                     |
| $g_{fe}$                        | Forward Transconductance <sup>④</sup>               | 2.9  | 5.1  | —         | S                    | $V_{CE} = 100V, I_C = 9.0A$                           |
| $I_{CES}$                       | Zero Gate Voltage Collector Current                 | —    | —    | 250       | $\mu A$              | $V_{GE} = 0V, V_{CE} = 600V$                          |
|                                 |                                                     | —    | —    | 1700      |                      | $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$ |
| $V_{FM}$                        | Diode Forward Voltage Drop                          | —    | 1.4  | 1.7       | V                    | $I_C = 8.0A$ See Fig. 13                              |
|                                 |                                                     | —    | 1.3  | 1.6       |                      | $I_C = 8.0A, T_J = 150^\circ\text{C}$                 |
| $I_{GES}$                       | Gate-to-Emitter Leakage Current                     | —    | —    | $\pm 100$ | nA                   | $V_{GE} = \pm 20V$                                    |

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

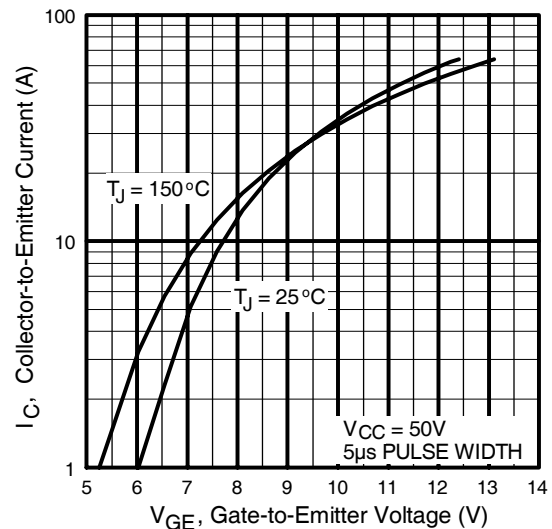
|                  | Parameter                                        | Min. | Typ. | Max. | Units      | Conditions                                                                                                                                                               |
|------------------|--------------------------------------------------|------|------|------|------------|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| $Q_g$            | Total Gate Charge (turn-on)                      | —    | 27   | 40   | nC         | $I_C = 9.0A$                                                                                                                                                             |
| $Q_{ge}$         | Gate - Emitter Charge (turn-on)                  | —    | 4.2  | 6.2  |            | $V_{CC} = 400V$ See Fig. 8                                                                                                                                               |
| $Q_{gc}$         | Gate - Collector Charge (turn-on)                | —    | 9.9  | 15   |            | $V_{GE} = 15V$                                                                                                                                                           |
| $t_{d(on)}$      | Turn-On Delay Time                               | —    | 43   | —    | ns         | $T_J = 25^\circ\text{C}$                                                                                                                                                 |
| $t_r$            | Rise Time                                        | —    | 20   | —    |            | $I_C = 9.0A, V_{CC} = 480V$                                                                                                                                              |
| $t_{d(off)}$     | Turn-Off Delay Time                              | —    | 240  | 360  |            | $V_{GE} = 15V, R_G = 50\Omega$                                                                                                                                           |
| $t_f$            | Fall Time                                        | —    | 150  | 220  |            | Energy losses include "tail" and diode reverse recovery. See Fig. 9, 10, 18                                                                                              |
| $E_{on}$         | Turn-On Switching Loss                           | —    | 0.25 | —    | mJ         | $T_J = 150^\circ\text{C}$ , See Fig. 11, 18<br>$I_C = 9.0A, V_{CC} = 480V$<br>$V_{GE} = 15V, R_G = 50\Omega$<br>Energy losses include "tail" and diode reverse recovery. |
| $E_{off}$        | Turn-Off Switching Loss                          | —    | 0.64 | —    |            |                                                                                                                                                                          |
| $E_{ts}$         | Total Switching Loss                             | —    | 0.89 | 1.3  |            |                                                                                                                                                                          |
| $t_{d(on)}$      | Turn-On Delay Time                               | —    | 41   | —    | ns         | $T_J = 150^\circ\text{C}$ , See Fig. 11, 18<br>$I_C = 9.0A, V_{CC} = 480V$<br>$V_{GE} = 15V, R_G = 50\Omega$<br>Energy losses include "tail" and diode reverse recovery. |
| $t_r$            | Rise Time                                        | —    | 22   | —    |            |                                                                                                                                                                          |
| $t_{d(off)}$     | Turn-Off Delay Time                              | —    | 320  | —    |            |                                                                                                                                                                          |
| $t_f$            | Fall Time                                        | —    | 290  | —    |            |                                                                                                                                                                          |
| $E_{ts}$         | Total Switching Loss                             | —    | 1.35 | —    | mJ         |                                                                                                                                                                          |
| $L_E$            | Internal Emitter Inductance                      | —    | 7.5  | —    | nH         | Measured 5mm from package                                                                                                                                                |
| $C_{ies}$        | Input Capacitance                                | —    | 540  | —    | pF         | $V_{GE} = 0V$                                                                                                                                                            |
| $C_{oes}$        | Output Capacitance                               | —    | 37   | —    |            | $V_{CC} = 30V$ See Fig. 7                                                                                                                                                |
| $C_{res}$        | Reverse Transfer Capacitance                     | —    | 7.0  | —    |            | $f = 1.0MHz$                                                                                                                                                             |
| $t_{rr}$         | Diode Reverse Recovery Time                      | —    | 37   | 55   | ns         | $T_J = 25^\circ\text{C}$ See Fig. 14                                                                                                                                     |
|                  |                                                  | —    | 55   | 90   |            | $T_J = 125^\circ\text{C}$                                                                                                                                                |
| $I_{rr}$         | Diode Peak Reverse Recovery Current              | —    | 3.5  | 5.0  | A          | $T_J = 25^\circ\text{C}$ See Fig. 15                                                                                                                                     |
|                  |                                                  | —    | 4.5  | 8.0  |            | $T_J = 125^\circ\text{C}$                                                                                                                                                |
| $Q_{rr}$         | Diode Reverse Recovery Charge                    | —    | 65   | 138  | nC         | $T_J = 25^\circ\text{C}$ See Fig. 16                                                                                                                                     |
|                  |                                                  | —    | 124  | 360  |            | $T_J = 125^\circ\text{C}$                                                                                                                                                |
| $di_{(rec)M}/dt$ | Diode Peak Rate of Fall of Recovery During $t_b$ | —    | 240  | —    | A/ $\mu s$ | $T_J = 25^\circ\text{C}$ See Fig. 17                                                                                                                                     |
|                  |                                                  | —    | 210  | —    |            | $T_J = 125^\circ\text{C}$                                                                                                                                                |



**Fig. 1 - Typical Load Current vs. Frequency**  
(Load Current =  $I_{\text{RMS}}$  of fundamental)



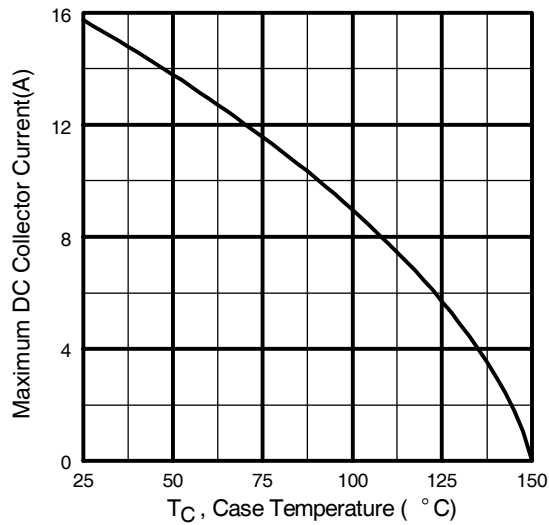
**Fig. 2 - Typical Output Characteristics**



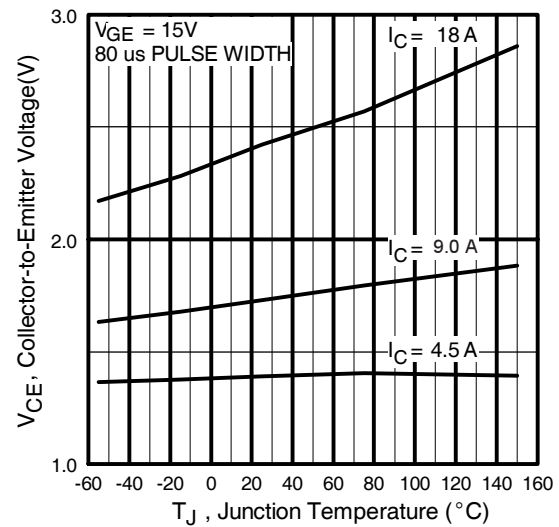
**Fig. 3 - Typical Transfer Characteristics**

# IRG4BC20FDPbF

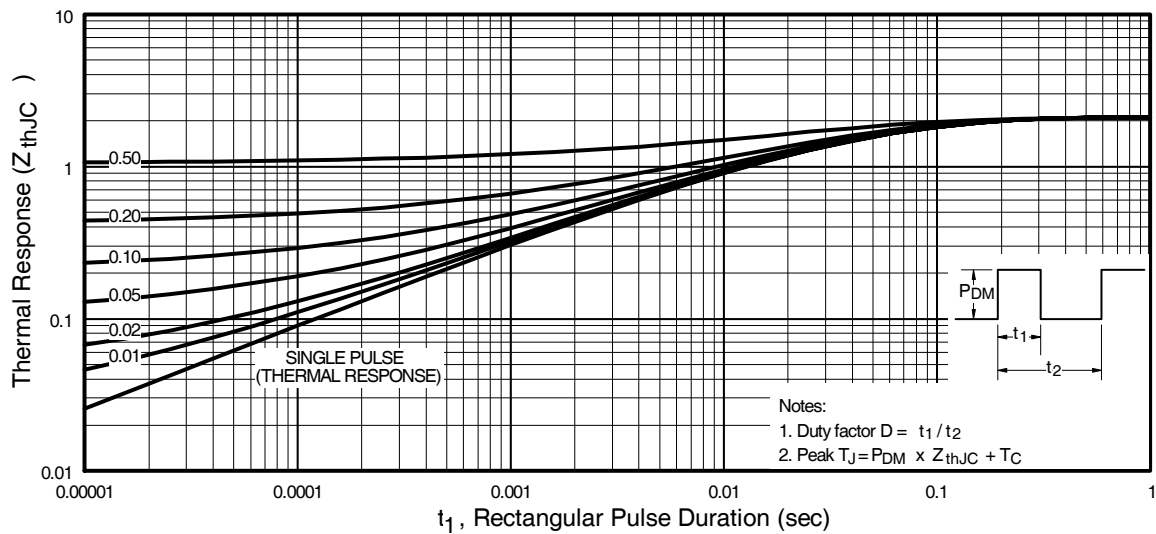
International  
**IR** Rectifier



**Fig. 4** - Maximum Collector Current vs. Case Temperature

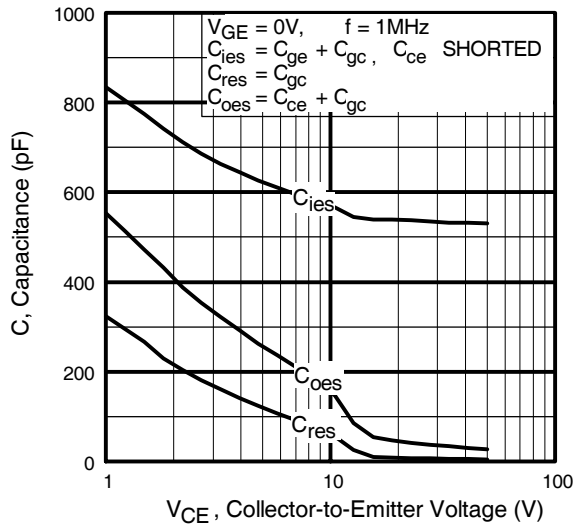


**Fig. 5** - Typical Collector-to-Emitter Voltage vs. Junction Temperature

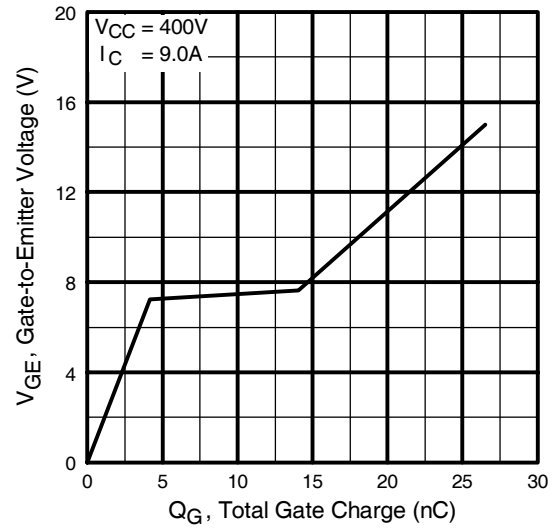


**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case

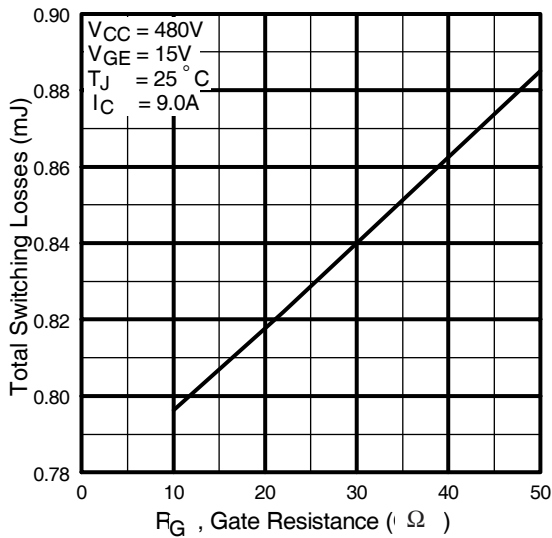
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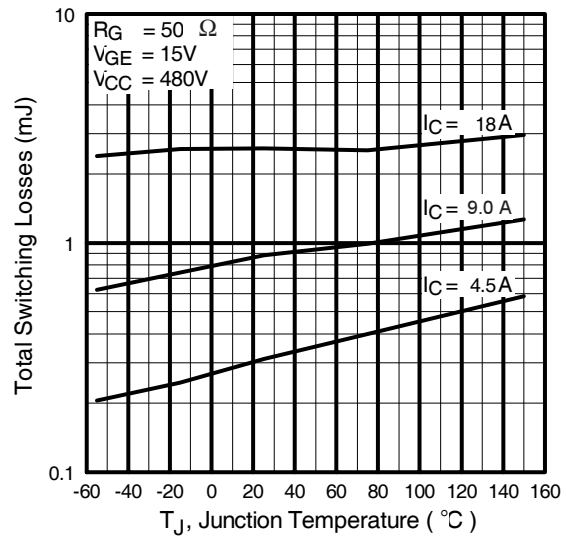
**Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage**



**Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage**



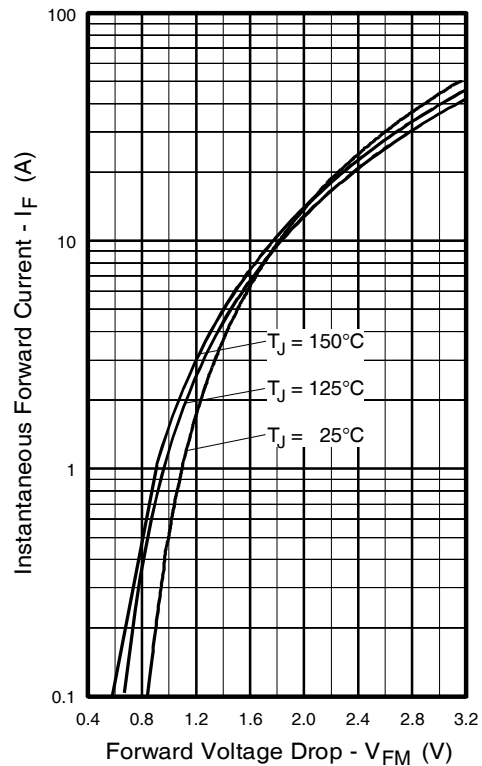
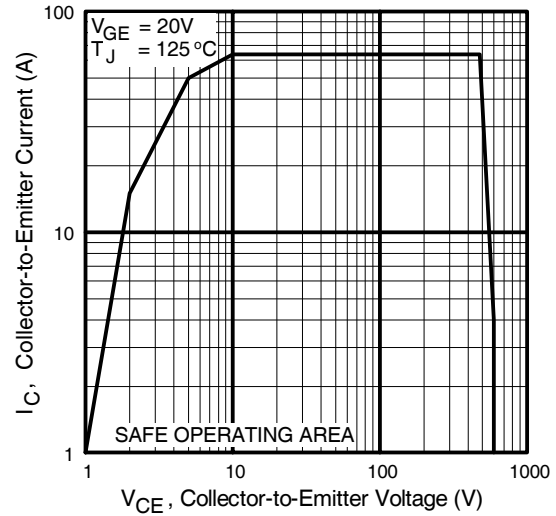
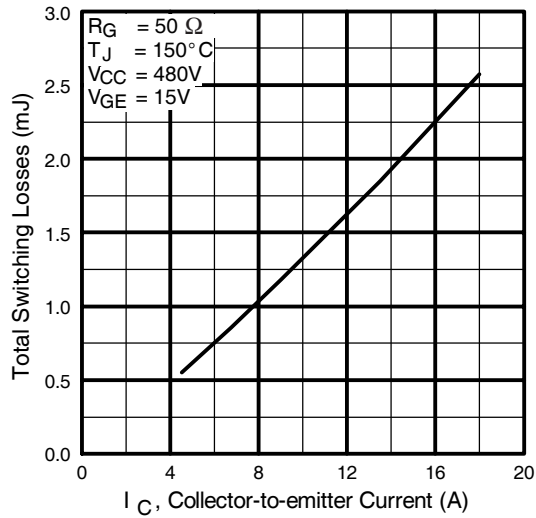
**Fig. 9 - Typical Switching Losses vs. Gate Resistance**

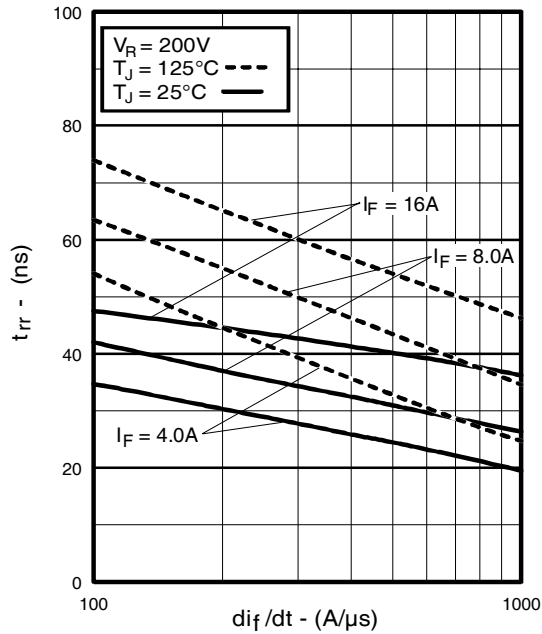


**Fig. 10 - Typical Switching Losses vs. Junction Temperature**

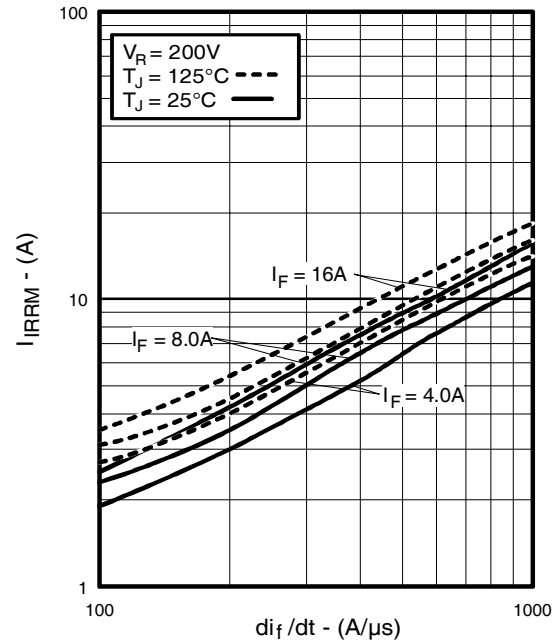
# IRG4BC20FDPbF

International  
**IR** Rectifier

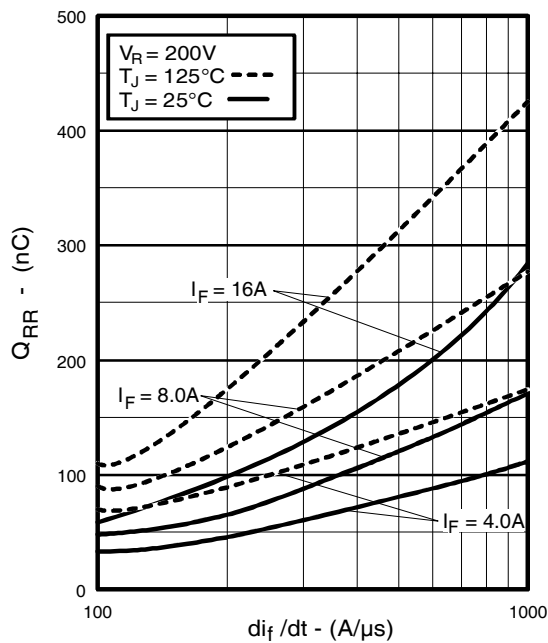




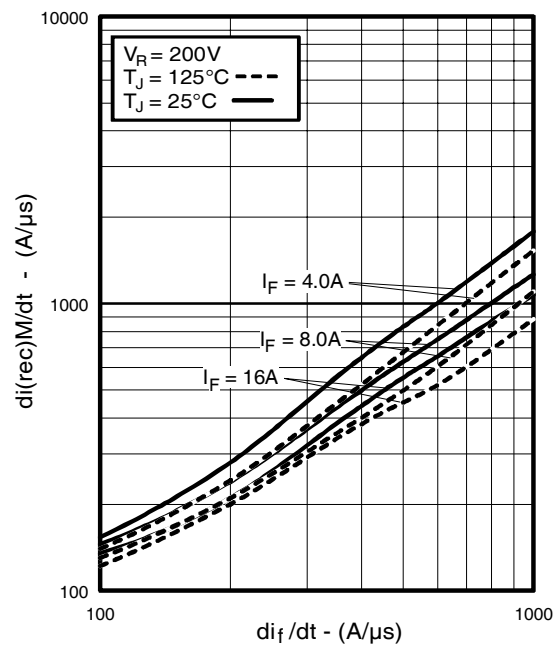
**Fig. 14 - Typical Reverse Recovery vs.  $di_f/dt$**



**Fig. 15 - Typical Recovery Current vs.  $di_f/dt$**



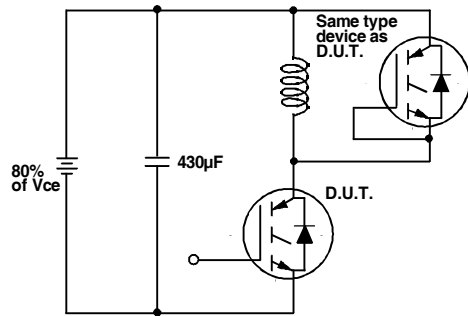
**Fig. 16 - Typical Stored Charge vs.  $di_f/dt$**



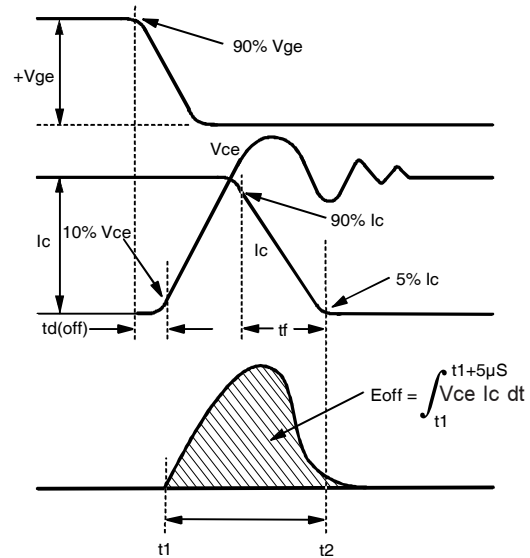
**Fig. 17 - Typical  $di_{(rec)M}/dt$  vs.  $di_f/dt$**

# IRG4BC20FDPbF

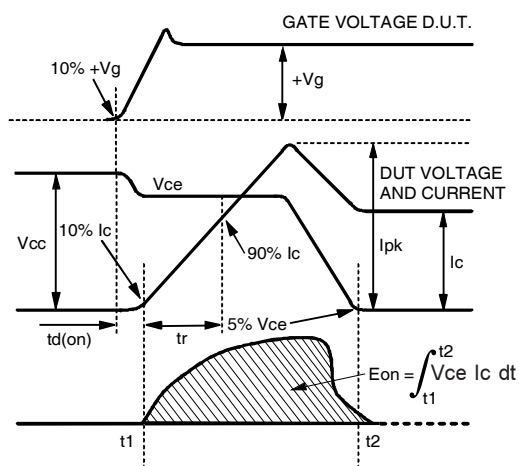
International  
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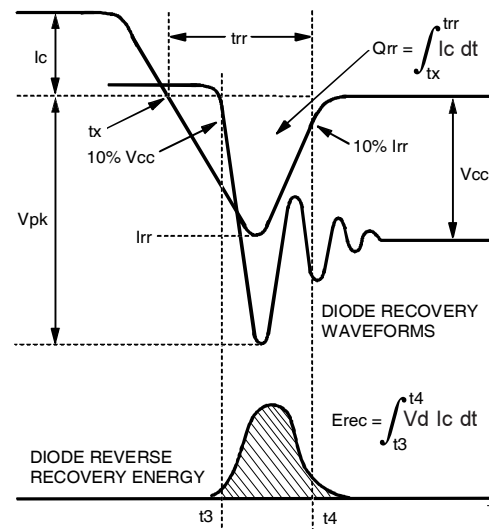
**Fig. 18a** - Test Circuit for Measurement of  $I_{LM}$ ,  $E_{on}$ ,  $E_{off}(\text{diode})$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$ ,  $t_{d(on)}$ ,  $t_r$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18b** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{off}$ ,  $t_{d(off)}$ ,  $t_f$



**Fig. 18c** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{on}$ ,  $t_{d(on)}$ ,  $t_r$



**Fig. 18d** - Test Waveforms for Circuit of Fig. 18a, Defining  $E_{rec}$ ,  $t_{rr}$ ,  $Q_{rr}$ ,  $I_{rr}$

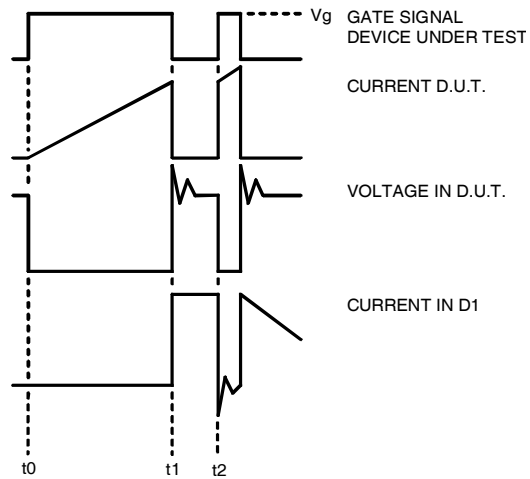


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

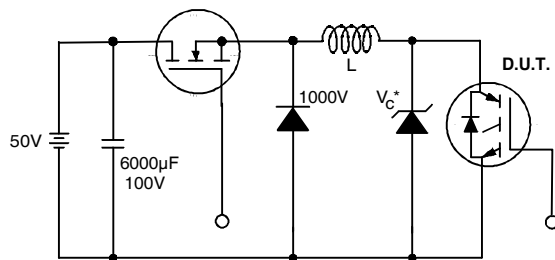


Figure 19. Clamped Inductive Load Test Circuit

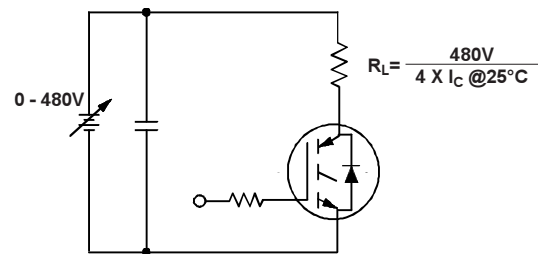


Figure 20. Pulsed Collector Current Test Circuit

# IRG4BC20FDPbF

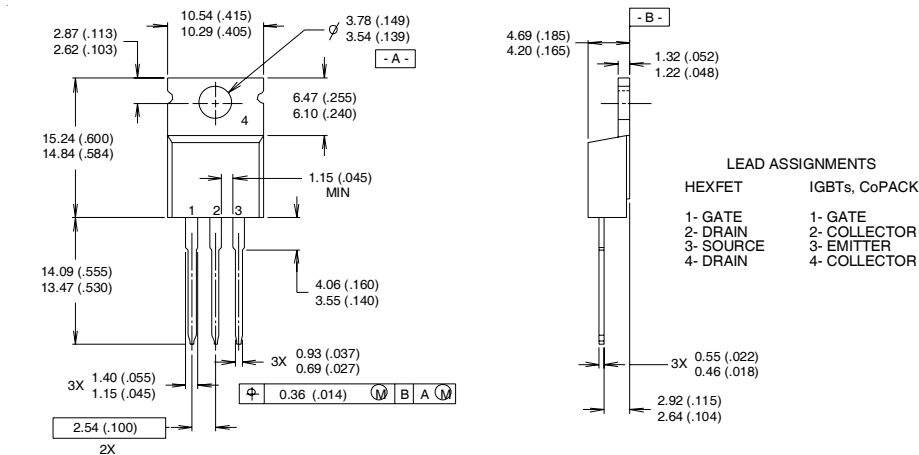
International  
**IR** Rectifier

## Notes:

- ① Repetitive rating:  $V_{GE}=20V$ ; pulse width limited by maximum junction temperature (figure 20)
- ②  $V_{CC}=80\%(V_{CES})$ ,  $V_{GE}=20V$ ,  $L=10\mu H$ ,  $R_G = 50\Omega$  (figure 19)
- ③ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ④ Pulse width  $5.0\mu s$ , single shot.

## TO-220AB Package Outline

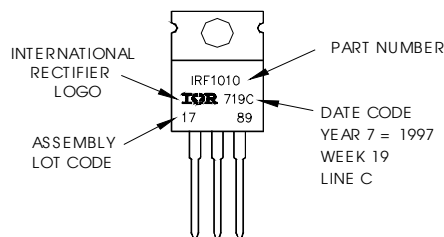
Dimensions are shown in millimeters (inches)



- NOTES:
- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
  - 2 CONTROLLING DIMENSION : INCH
  - 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
  - 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

## TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010  
LOT CODE 1789  
ASSEMBLED ON WW 19, 1997  
IN THE ASSEMBLY LINE "C"  
**Note:** "P" in assembly line  
position indicates "Lead-Free"



Data and specifications subject to change without notice.

International  
**IR** Rectifier

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TAC Fax: (310) 252-7903

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Note: For the most current drawings please refer to the IR website at:  
<http://www.irf.com/package/>